

## Transistors

EMH2 / UMH2N / IMH2A

# General purpose (dual digital transistors)

## EMH2 / UMH2N / IMH2A

## ●Features

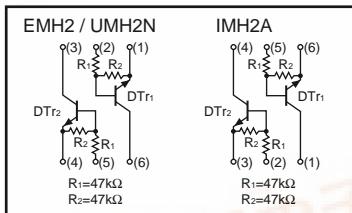
- 1) Two DTC144Es chips in a EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

## ●Structure

Epitaxial planar type  
NPN silicon transistor  
(Built-in resistor type)

The following characteristics apply to both DTr<sub>1</sub> and DTr<sub>2</sub>.

## ●Equivalent circuit



## ●Packaging specifications

Type	Package	Taping		
		T2R	TN	T110
	Basic ordering unit (pieces)	8000	3000	3000
EMH2		○	-	-
UMH2N		-	○	-
IMH2A		-	-	○

## ●External dimensions (Units : mm)

EMH2	ROHM : EMT6	Abbreviated symbol : H2
		All terminals have same dimensions
UMH2N	ROHM : UMT6 EIAJ : SC-88	Abbreviated symbol : H2
		All terminals have same dimensions
IMH2A	ROHM : SMT6 EIAJ : SC-74	Abbreviated symbol : H2
		All terminals have same dimensions

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### ● Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Supply voltage	$V_{cc}$	50	V
Input voltage	$V_{in}$	40	V
		-10	
Output current	$I_o$	30	mA
		100	
Power dissipation	$P_d$	150 (TOTAL)	mW <sup>*1</sup>
		300 (TOTAL)	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

\*1 120mW per element must not be exceeded.

\*2 200mW per element must not be exceeded.

### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{l(\text{off})}$	—	—	0.5	V	$V_{cc}=5\text{V}$ , $I_o=100\mu\text{A}$
	$V_{l(\text{on})}$	3	—	—		$V_o=0.3\text{V}$ , $I_o=2\text{mA}$
Output voltage	$V_{o(\text{on})}$	—	0.1	0.3	V	$I_o/I_l=10\text{mA}/0.5\text{mA}$
Input current	$I_l$	—	—	0.18	mA	$V_l=5\text{V}$
Output current	$I_{o(\text{off})}$	—	—	0.5	$\mu\text{A}$	$V_{cc}=50\text{V}$ , $V_l=0\text{V}$
DC current gain	$G_i$	68	—	—	—	$V_{o}=5\text{V}$ , $I_o=5\text{mA}$
Transition frequency	$f_T$	—	250	—	MHz	$V_{ce}=10\text{mA}$ , $I_e=-5\text{mA}$ , $f=100\text{MHz}$ *
Input resistance	$R_i$	32.9	47	61.1	k $\Omega$	—
Resistance ratio	$R_2/R_1$	0.8	1	1.2	—	—

\* Transition frequency of the device

### ● Electrical characteristic curves

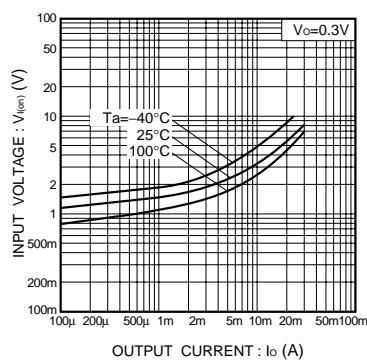


Fig.1 Input voltage vs. output current  
(ON characteristics)

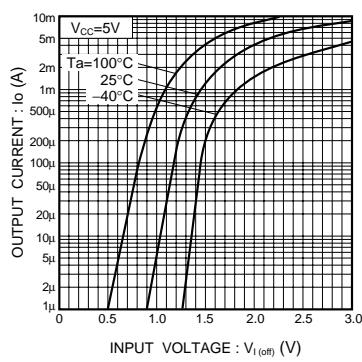


Fig.2 Output current vs. input voltage  
(OFF characteristics)

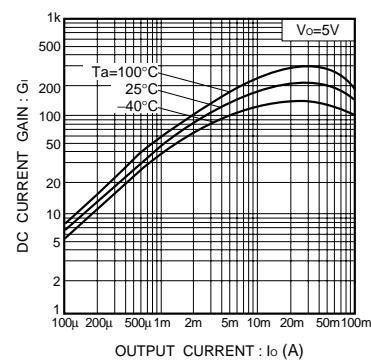


Fig.3 DC current gain vs. output current

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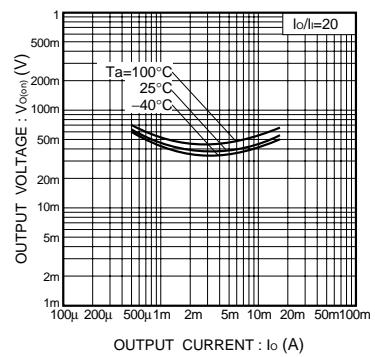


Fig.4 Output voltage vs. output current